ne<mark>x</mark>peria

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <u>http://www.nxp.com</u>, <u>http://www.philips.com/</u> or <u>http://www.semiconductors.philips.com/</u>, use <u>http://www.nexperia.com</u>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

Rev. 4 — 19 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview

Type number	Package		NPN/PNP PNP/PNP		······································		U
	NXP	JEITA	complement	complement	configuration		
PEMH18	SOT666	-	PEMD18	PEMB18	ultra small and flat lead		
PUMH18	SOT363	SC-88	PUMD18	PUMB18	very small		

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2.	Quick reference data						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per transistor							
V _{CEO}	collector-emitter voltage	open base	-	-	50	V	
lo	output current		-	-	100	mA	
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ	
R2/R1	bias resistor ratio		1.7	2.1	2.6		



- Reduces component countReduces pick and place costs
- AEC-Q101 qualified

| | 2 3 *sym063*

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

2. Pinning information

Table 3.	Pinning					
Pin	Description	Simplified outline	Graphic symbol			
1	GND (emitter) TR1					
2	input (base) TR1					
3	output (collector) TR2					
4	GND (emitter) TR2					
5	input (base) TR2					
6	output (collector) TR1	001aab555				

3. Ordering information

Table 4. Ordering information					
Type number Package					
	Name	Description	Version		
PEMH18	-	plastic surface-mounted package; 6 leads	SOT666		
PUMH18	SC-88	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Table 5.	Marking codes	

Type number	Marking code ^[1]
PEMH18	6C
PUMH18	H5*

[1] * = placeholder for manufacturing site code

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

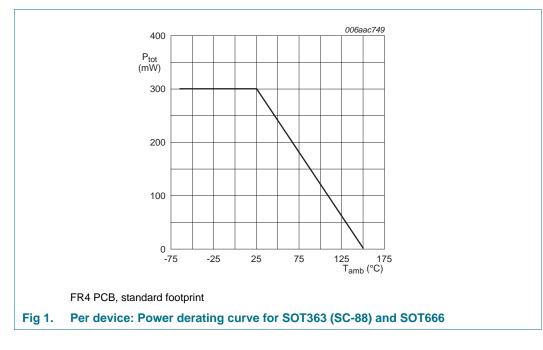
5. Limiting values

Symbol	Parameter	Conditions	М	in Max	Unit
Per transi	stor				
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	7	V
VI	input voltage				
	positive		-	+20	V
	negative		-	-7	V
lo	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH18 (SOT666)		[1][2] _	200	mW
	PUMH18 (SOT363)		<u>[1]</u> -	200	mW
Per device	;				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH18 (SOT666)		[1][2] _	300	mW
	PUMH18 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-6	65 +150	°C
T _{stg}	storage temperature		-6	65 +150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



6. Thermal characteristics

Symbol	Parameter	Conditions	Mir	і Тур	Max	Unit
Per transi	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH18 (SOT666)		[1][2]	-	625	K/W
	PUMH18 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device	9					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH18 (SOT666)		<u>[1][2]</u> _	-	417	K/W
	PUMH18 (SOT363)		<u>[1]</u> -	-	417	K/W

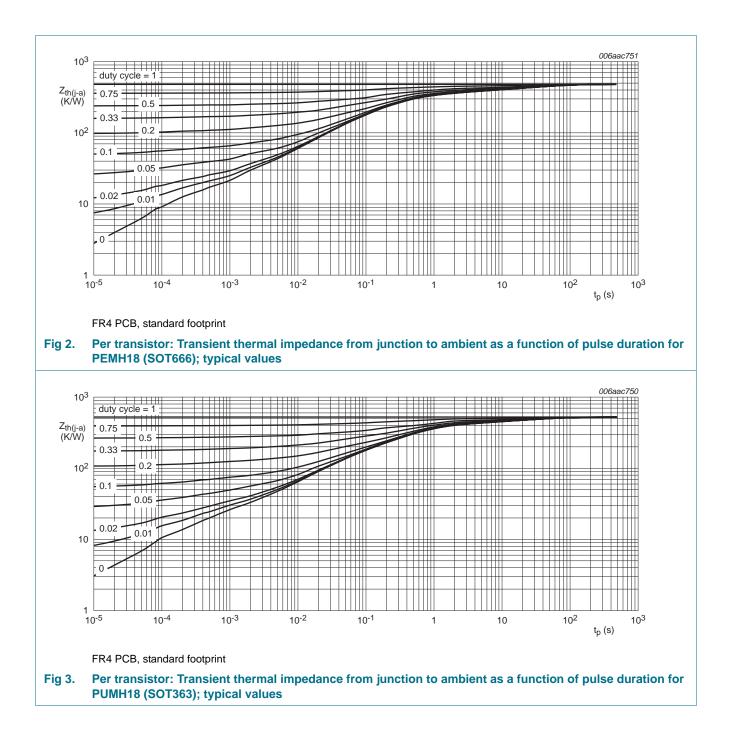
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMH18_PUMH18 Product data sheet

PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

7. Characteristics

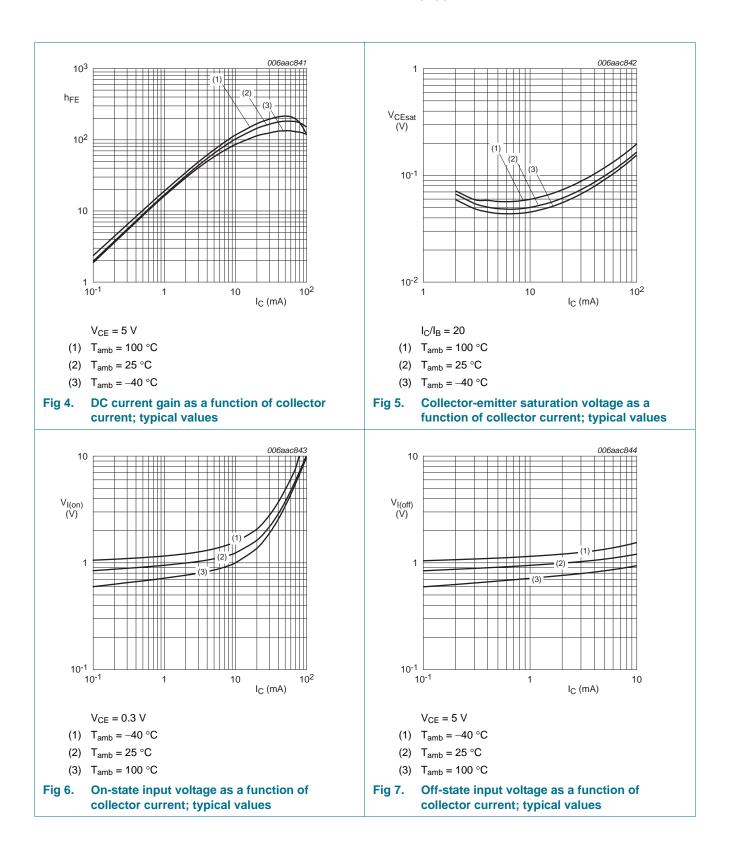
Table 8. $T_{amb} = 25$	Characteristics 5 °C unless otherwise spe	ecified.						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Per trans	Per transistor							
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA		
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μΑ		
	current	$\label{eq:VCE} \begin{array}{l} V_{CE} = 30 \; V; \; I_{B} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$	-	-	5	μA		
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	600	μΑ		
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	50	-	-			
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 10 mA; I_{B} = 0.5 mA	-	-	100	mV		
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A	-	0.9	0.3	V		
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I _C = 20 mA	2.5	1.5	-	V		
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ		
R2/R1	bias resistor ratio		1.7	2.1	2.6			
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF		
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	<u>[1]</u> _	230	-	MHz		

[1] Characteristics of built-in transistor

PEMH18_PUMH18 Product data sheet

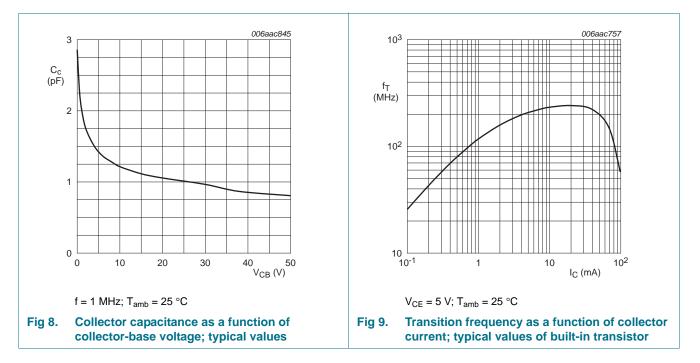
PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

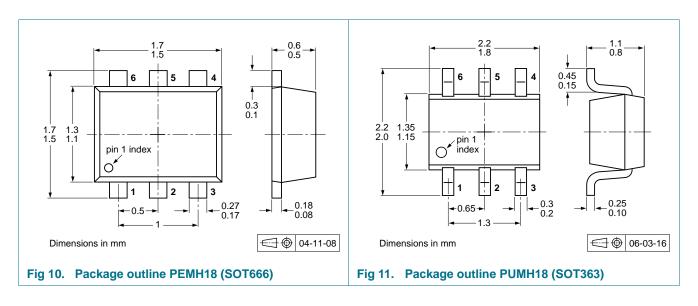


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMH18_PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

10. Packing information

Table 9. Packing methods

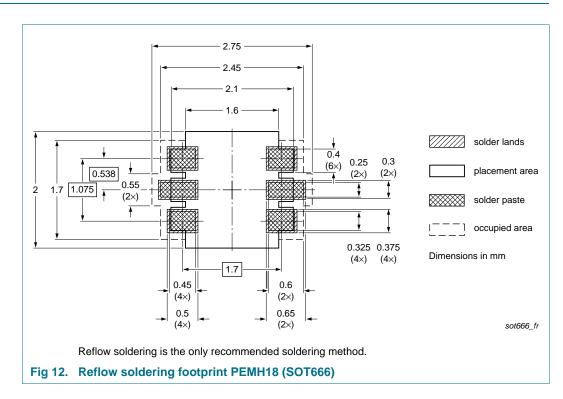
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	Package Description			Packing quantity			
number				3000	4000	8000	10000	
PEMH18	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-	
		4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMH18	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165	

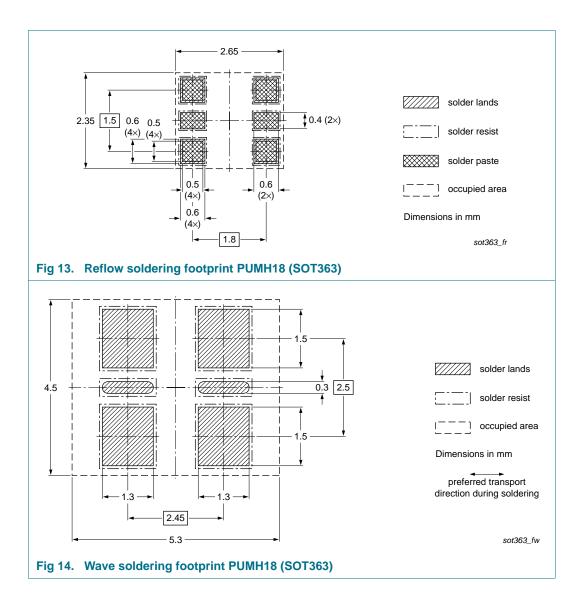
[1] For further information and the availability of packing methods, see Section 14.

- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering



NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



PEMH18_PUMH18 Product data sheet NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

12. Revision history

Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH18_PUMH18 v.4	20111219	Product data sheet	-	PEMH18_PUMH18 v.3
Modifications:	 Section 4 "M Figure 1 to 3 Section 6 "TI Figure 4 to 7 Table 8 "Cha Section 8 "Te Section 11 "S 	roduct profile": updated arking": updated (, <u>8</u> and <u>9</u> : added hermal characteristics": up (: updated aracteristics": I _{CEO} updated est information": added Soldering": added Legal information": updated	, f _T added	
PEMH18_PUMH18 v.3	20050211	Product data sheet	-	PEMH18_PUMH18 v.2
PEMH18_PUMH18 v.2	20040414	Product data sheet	-	PUMH18 v.1
PUMH18 v.1	20031016	Product specification	-	-

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof. Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

PEMH18_PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

Export control - This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

14. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

15. Contents

15	Contents 14
14	Contact information 13
13.4	Trademarks 13
13.3	Disclaimers 12
13.2	Definitions 12
13.1	Data sheet status 12
13	Legal information 12
12	Revision history 11
11	Soldering 9
10	Packing information 9
9	Package outline 8
8.1	Quality information
8	Test information
7	Characteristics
6	Thermal characteristics 4
5	Limiting values
•	
3 4	Marking
3	Ordering information
2	Pinning information
1.3	Quick reference data
1.2	Features and benefits 1 Applications 1
1.1 1.2	General description
1	Product profile 1
4	Draduct profile 4

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2011.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 19 December 2011 Document identifier: PEMH18_PUMH18